FAIRCHILD
SEMICONDUCTOR®

January 2009
QFET™

FQP8N80C/FQPF8N80C/FQPF8N80CYDTU

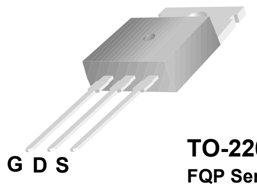
800V N-Channel MOSFET

General Description

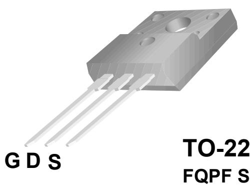
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies.

Features

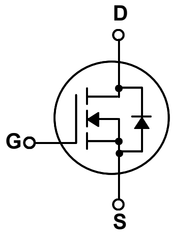
- 8A, 800V, $R_{DS(on)} = 1.55\Omega$ @V_{GS} = 10 V
- Low gate charge (typical 35 nC)
- Low Crss (typical 13 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHSCompliant



TO-220
FQP Series



TO-220F
FQPF Series



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		FQP8N80C	FQPF8N80C	Units
V_{DSS}	Drain-Source Voltage		800	800	V
I_D	Drain Current - Continuous (T_C = 25°C)		8	8 *	A
	- Continuous (T_C = 100°C)		5.1	5.1 *	A
I_{DM}	Drain Current - Pulsed	(Note 1)	32	32 *	A
V_{GSS}	Gate-Source Voltage		± 30	± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	850	850	mJ
I_{AR}	Avalanche Current	(Note 1)	8	8	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	17.8	17.8	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	4.5	V/ns
P_D	Power Dissipation (T_C = 25°C)		178	59	W
	- Derate above 25°C		1.43	0.48	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	-55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	300	°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP8N80C	FQPF8N80C	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.7	2.1	°C/W
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA	800	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C	--	0.5	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 800 V, V_{GS} = 0 V	--	--	10	µA
		V_{DS} = 640 V, T_C = 125°C	--	--	100	µA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 4 A	--	1.29	1.55	Ω
g_{FS}	Forward Transconductance	V_{DS} = 50 V, I_D = 4 A (Note 4)	--	5.6	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	1580	2050	pF
C_{oss}	Output Capacitance		--	135	175	pF
C_{rss}	Reverse Transfer Capacitance		--	13	17	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400 V, I_D = 8 A, R_G = 25 Ω (Note 4, 5)	--	40	90	ns
t_r	Turn-On Rise Time		--	110	230	ns
$t_{d(off)}$	Turn-Off Delay Time		--	65	140	ns
t_f	Turn-Off Fall Time		--	70	150	ns
Q_g	Total Gate Charge	V_{DS} = 640 V, I_D = 8 A, V_{GS} = 10 V (Note 4, 5)	--	35	45	nC
Q_{gs}	Gate-Source Charge		--	10	--	nC
Q_{gd}	Gate-Drain Charge		--	14	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	8	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	32	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 8 A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 8 A, dI_F / dt = 100 A/µs (Note 4)	--	690	--	ns
Q_{rr}	Reverse Recovery Charge		--	8.2	--	µC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 25mH, I_{AS} = 8A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. $I_{SD} \leq$ 8A, di/dt $\leq$ 200A/µs, $V_{DD} \leq BV_{DSS}$, Starting T_J = 25°C
4. Pulse Test : Pulse width $\leq$ 300µs, Duty cycle $\leq$ 2%
5. Essentially independent of operating temperature

Typical Characteristics

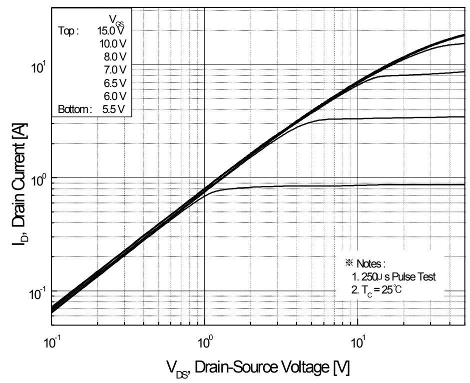


Figure 1. On-Region Characteristics

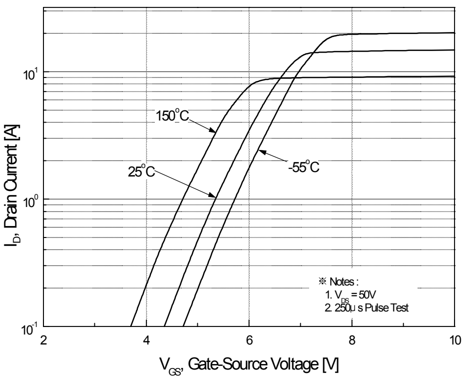


Figure 2. Transfer Characteristics

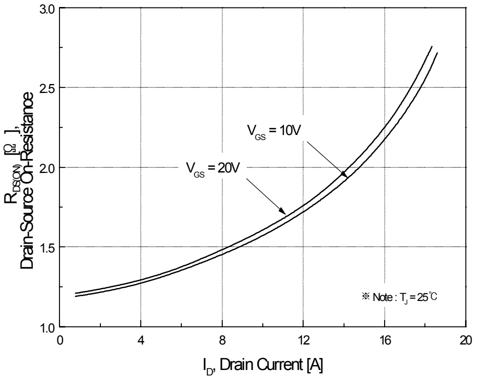


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

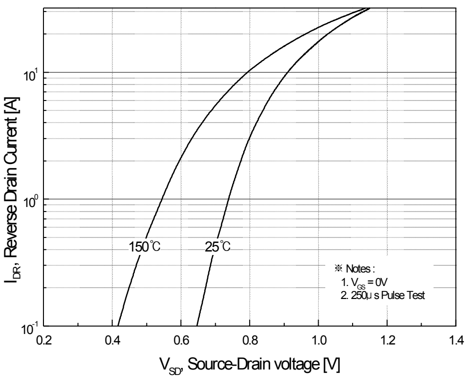


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

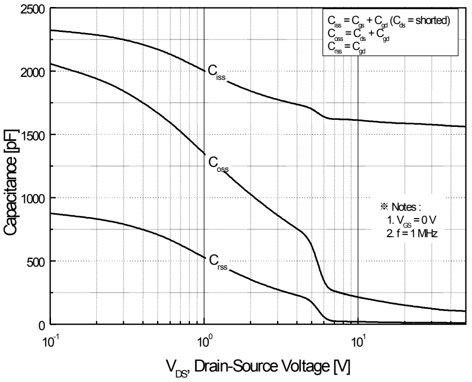


Figure 5. Capacitance Characteristics

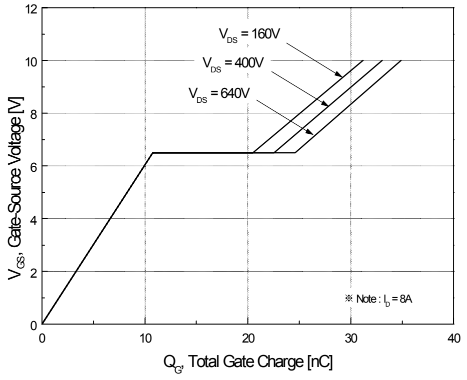


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

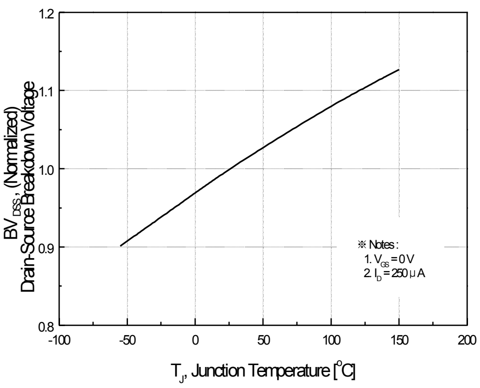


Figure 7. Breakdown Voltage Variation vs Temperature

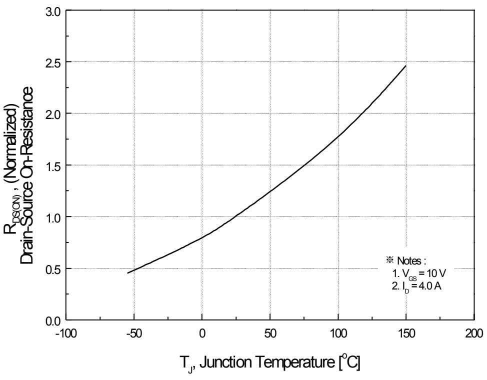


Figure 8. On-Resistance Variation vs Temperature

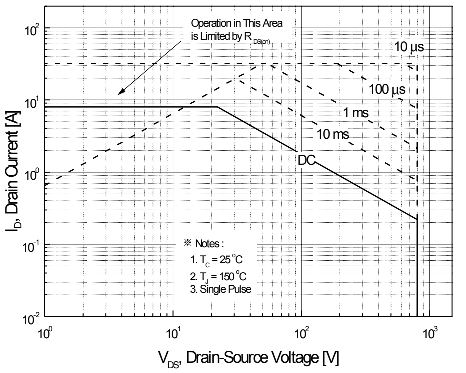


Figure 9-1. Maximum Safe Operating Area for FQP8N80C

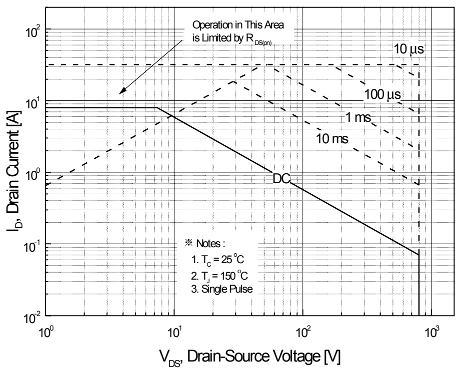


Figure 9-2. Maximum Safe Operating Area for FQPF8N80C

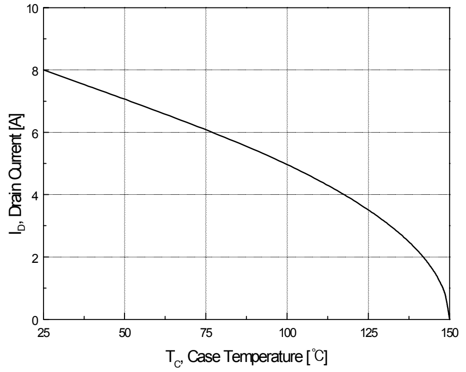


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

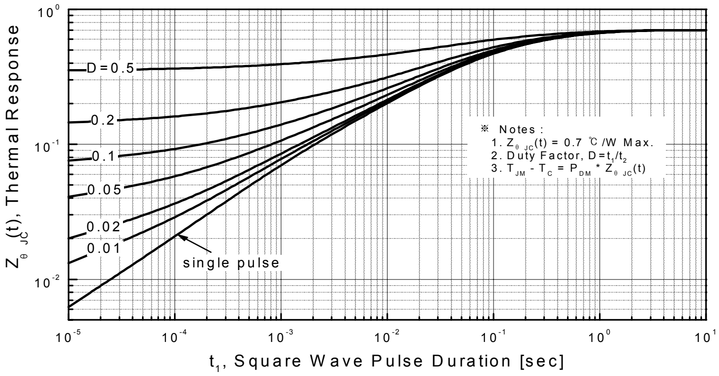


Figure 11-1. Transient Thermal Response Curve for FQP8N80C

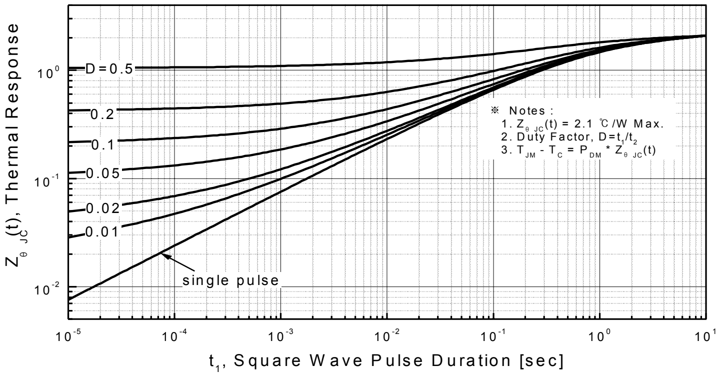
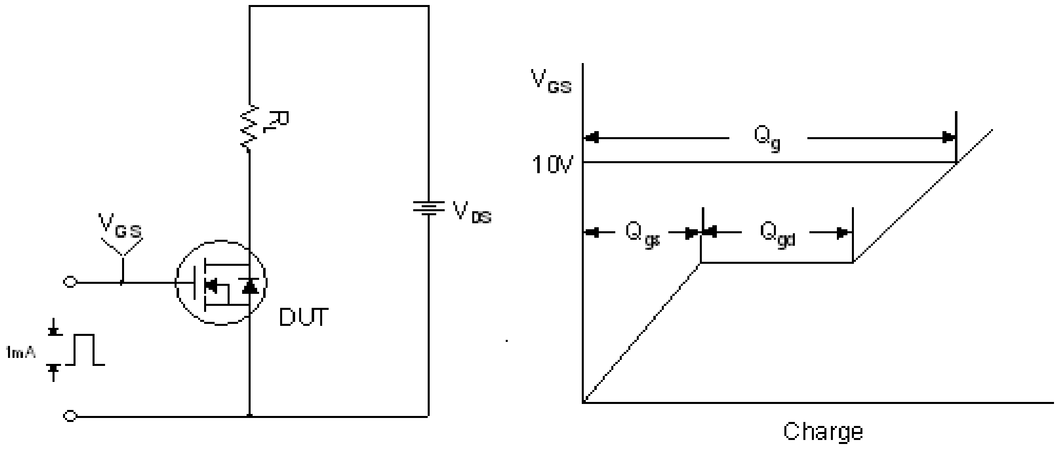
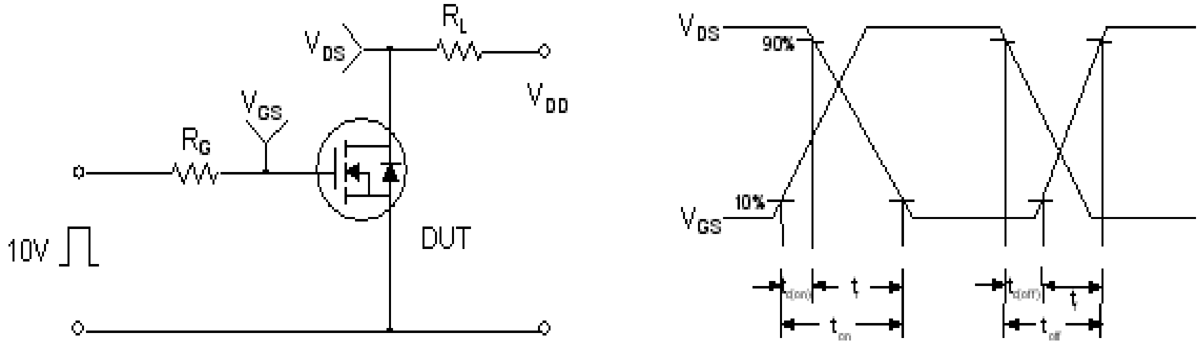


Figure 11-2. Transient Thermal Response Curve for FQPF8N80C

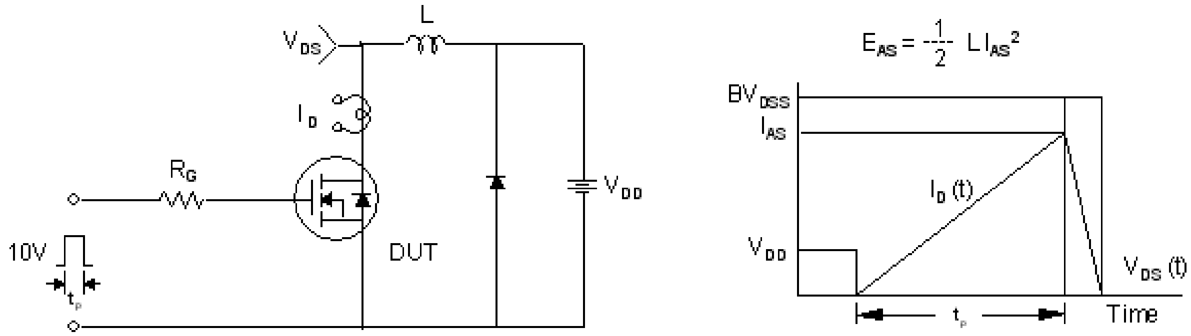
Gate Charge Test Circuit & Waveform



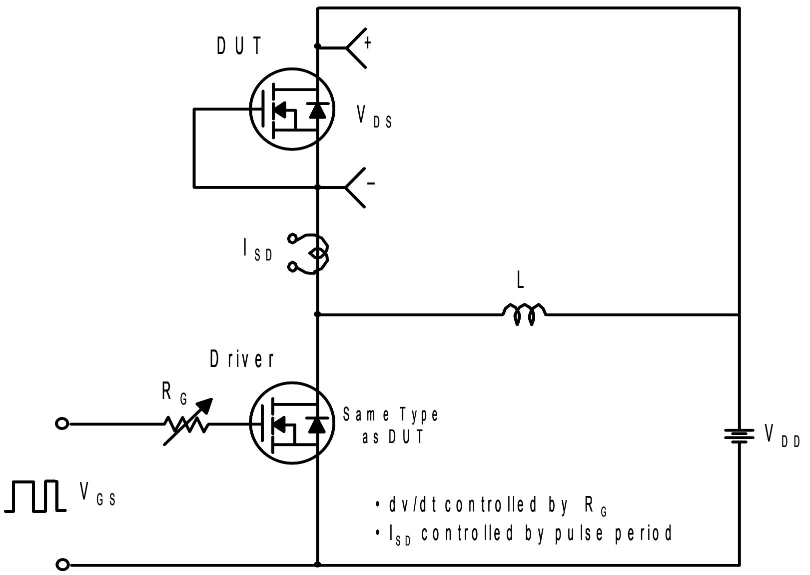
Resistive Switching Test Circuit & Waveforms

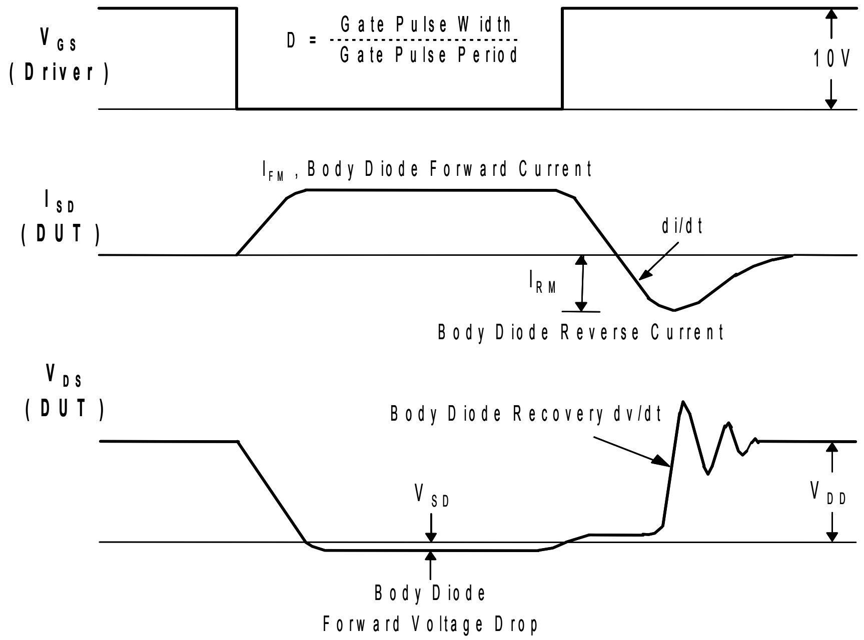


Unclamped Inductive Switching Test Circuit & Waveforms

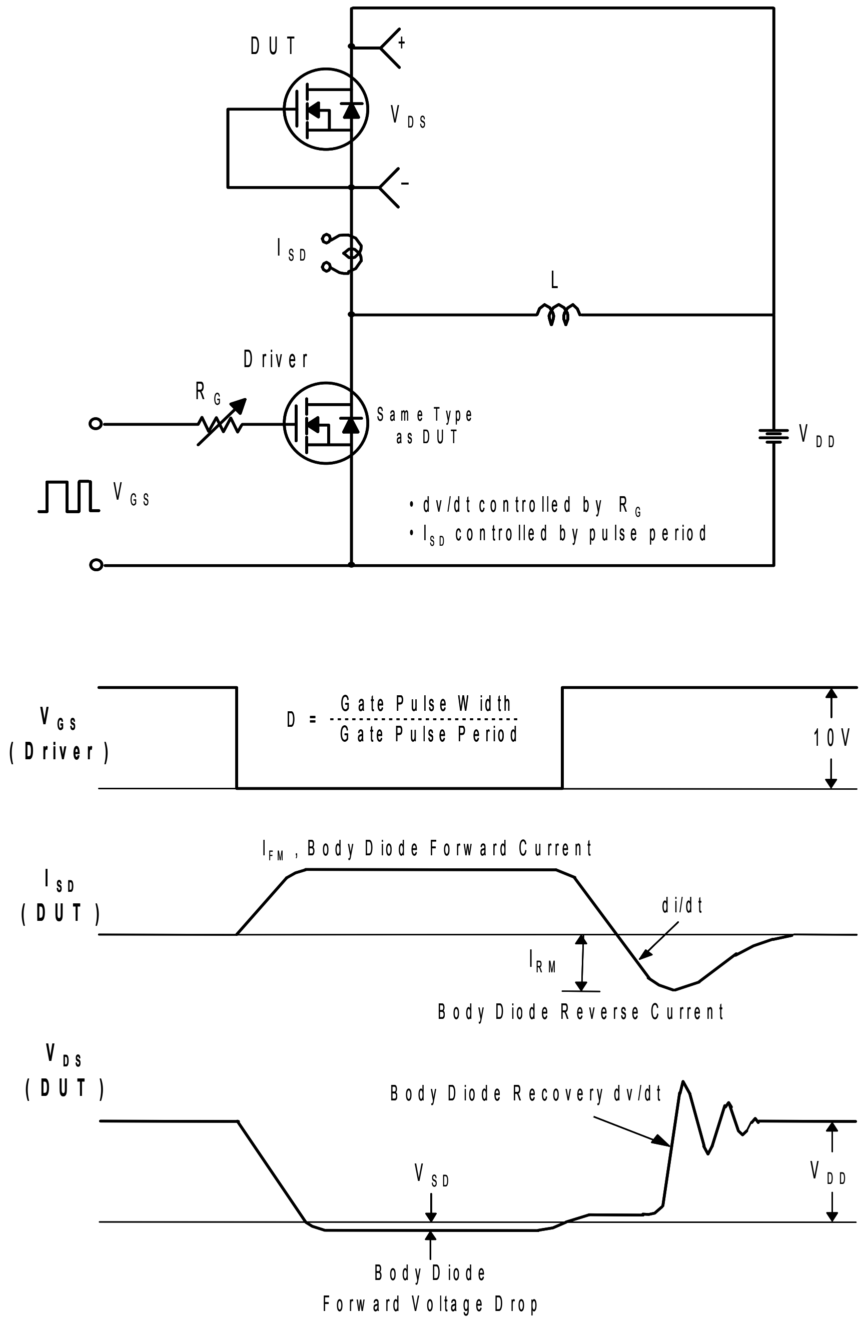


Peak Diode Recovery dv/dt Test Circuit & Waveforms



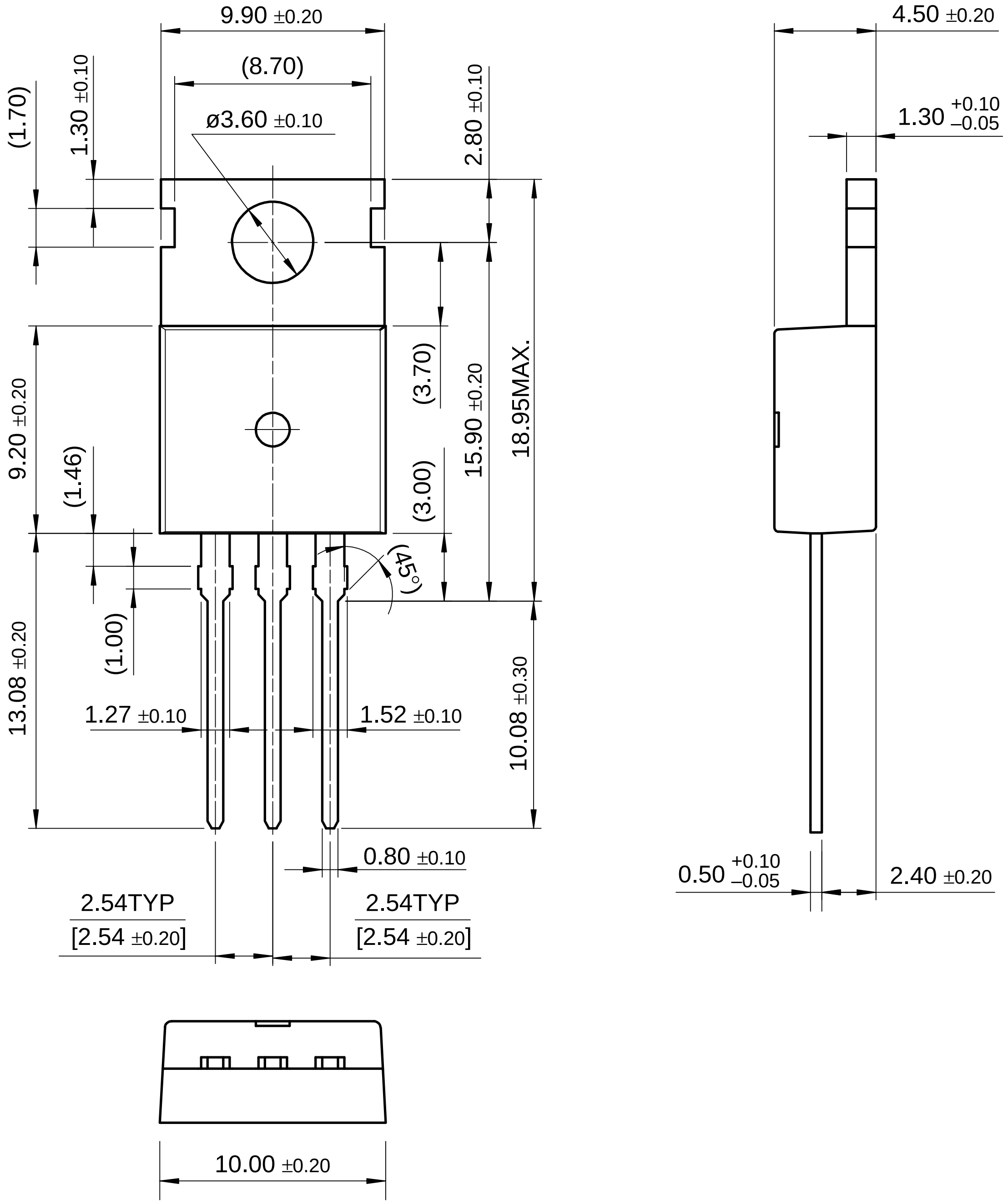


Peak Diode Recovery dv/dt Test Circuit & Waveforms



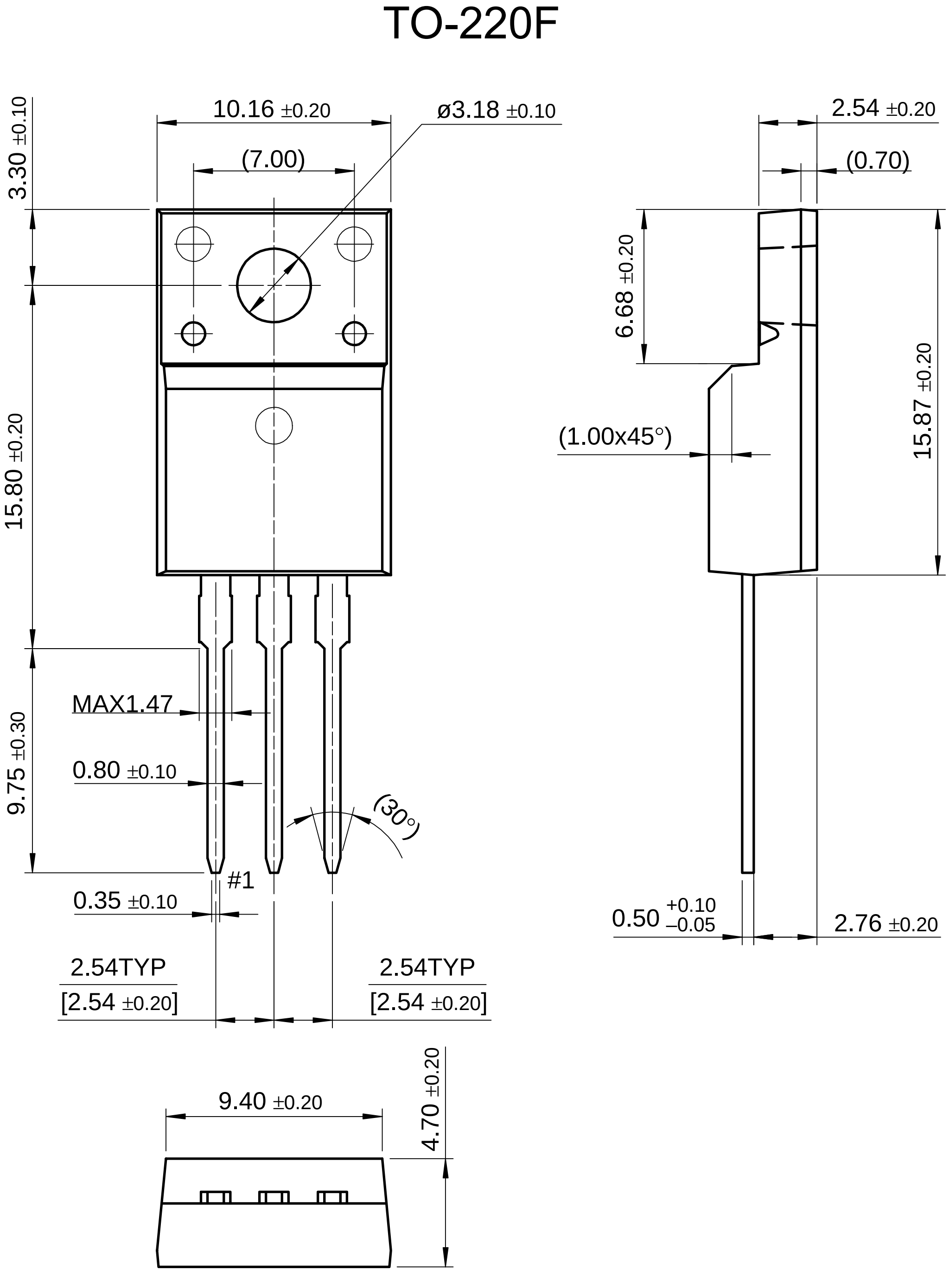
Package Dimensions

TO-220



Dimensions in Millimeters

Package Dimensions (Continued)



Dimensions in Millimeters

FAIRCHILD
SEMICONDUCTOR®

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
EcoSPARK®
EfficentMax™
EZSWITCH™ *
™
®
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FlashWriter® *
FPS™
F-PFS™

FRFET®
Global Power Resource^{SM}
Green FPS™
Green FPS™ e-Series™
GTO™
IntelliMAX™
ISOPLANAR™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MillerDrive™
MotionMax™
Motion-SPM™
OPTOLOGIC®
OPTOPLANAR®
®
PDP SPM™
Power-SPM™
PowerTrench®
PowerXS™

Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
™
Saving our world, 1mW /W /kW at a time™
SmartMax™
SMART START™
SPM®
STEALTH™
SuperFET™
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS™
SyncFET™
SYSTEM GENERAL ®
The Power Franchise®

the power franchise
TinyBoost™
TinyBuck™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
µSerDes™
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
XS™

* EZSWITCH™ and FlashWriter® are trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Farichild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Farichild strongly encourages customers to purchase Farichild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Farichild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Farichild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS
Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I37